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Supplementary Information

Synthesis and investigations of In_2S_3 : Ho^{3+} quantum dots on doping induce changes

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Experimental section

sample preparation and growth mechanism

Figure S1 presents the synthetic facility of In_2S_3 : Ho^{3+} nanoparticles by an easily reproducible gasliquid phase chemical deposition (this is an effective atomization doping method). The sufficiently stirring reactive solution is atomized to form the fine droplets with the average diameter of 2-4 μ m by using an ultrasonic nebulizer (the upper left portion of Fig. S1). The fog droplets will react with the H_2S gas taken by the flowing nitrogen in condensers with circulating water (25 °C). Finally, the reaction products were collected in a flat bottom flask placed in an ultrasonic water bath (the bottom left portion of Fig. S1). The waste gas was absorbed by the NaOH solution to avoid air pollution.

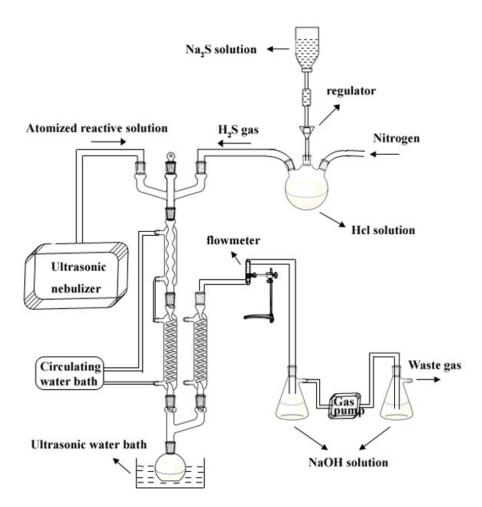


Fig. S1 The synthetic facility of In₂S₃:Ho³⁺ nanoparticles.

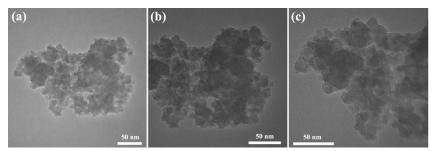


Fig. S2 (a) A low-magnification TEM image, (b) enlarged TEM image, (c) high-magnification TEM image of In_2S_3 :Ho³⁺ nanoparticles (concentration of dopant 0.75 at. %).

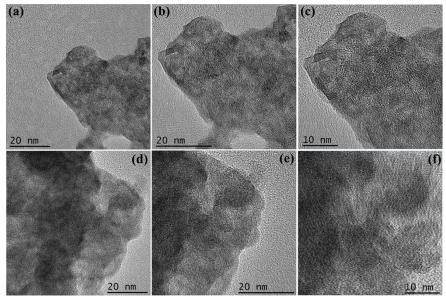


Fig. S3 HRTEM images with different magnification. (a), (b) and (c) for In_2S_3 :Ho³⁺ nanoparticles (concentration of dopant 0.75 at. %); (d), (e) and (f) for pure In_2S_3 nanoparticles.

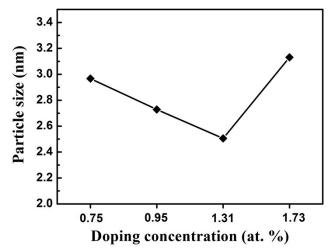


Fig. S4 The effect of Ho³⁺ concentration on the particle sizes of In₂S₃:Ho³⁺ nanoparticles.

First-principles calculations

As shown in Figure S5, two conventional cell models have been built. Figure S5a is corresponding to the ideal system of pure In_2S_3 ($In_{16}S_{24}$) with the optimized lattice constants (a = 10.774 Å), which agree well with the experimental values. Figures S5b is corresponding to $In_{15}Ho_1S_{24}$.

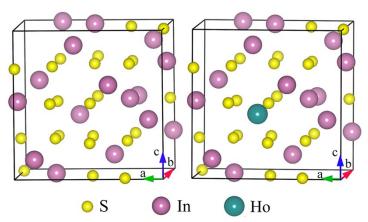


Fig. S5 Two calculation models: (a) the ideal system with no defect and doping ($In_{16}S_{24}$); (b) one In atom replaced by one Ho atom (Ho_{In}) ($In_{15}Ho_1S_{24}$).

Sample	ICP			EDX		
(the molar concentration	In	Но	Ho/In	In	Но	Ho/In
ratios of Ho ³⁺ and In ³⁺)	(ppm)	(ppm)	(Mass ratio)	(wt %)	(wt %)	(Mass ratio)
0.02	29.25	0.825	0.0282	68.26	1.91	0.0279
0.04	26.14	0.923	0.0353	68.65	2.38	0.0346
0.06	25.02	1.180	0.0472	68.28	3.24	0.0474
0.08	26.19	1.370	0.0523	73.80	3.89	0.0527

Table S1. Comparison of different doping concentrations In In_2S_3 : Ho^{3+} nanoparticles by the ICP and EDX methods.